

Small Signal Switching Diodes



CDSV3-202N-G/202P-G

Voltage: 80 Volts

Pd: 200mW

RoHS Device



Features

Designed for mounting on small surface.

High speed switching.

High mounting capability, strong surge withstand, high reliability.

Mechanical data

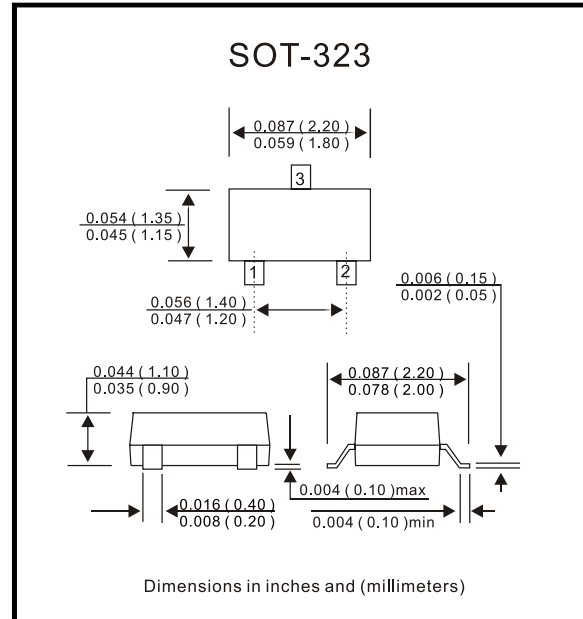
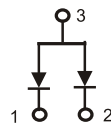
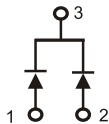
Case:SOT-323, molded plastic.

Terminals: Solder plated, solderable per MIL-STD-750, method 208.

Approx. weight: 0.006 gram

CDSV3-202N-G

CDSV3-202P-G



Maximum Ratings and Electrical Characteristics

(at Ta = 25°C unless otherwise noted)

Parameter	Condition	Symbol	Value	Unit
Repetitive peak reverse voltage		VRRM	80	V
Reverse voltage		VR	80	V
Peak forward current		IFM	300	mA
Surge peak forward current	T = 1.0 uS	IFSM	4	A
Power dissipation		Pd	200	mW
Maximum forward voltage	@ IF = 100 mA	VF	1.2	V
Maximum reverse current	@ VR = 70V	IR	0.1	uA
Max reverse recovery time	VR=6V,IF=IR=5mA,	Trr	4	nS
Maximum diode capacitnace	VR=6V, f=1MHz	CT	3.5	pF
Max. operation junction temperature		Tj	150	°C
Storage temperature		TSTG	-55 to +150	°C

RATING AND CHARACTERISTIC CURVES (CDSV3-202N-G/202P-G)

Fig. 1 - Forward characteristics(P Type)

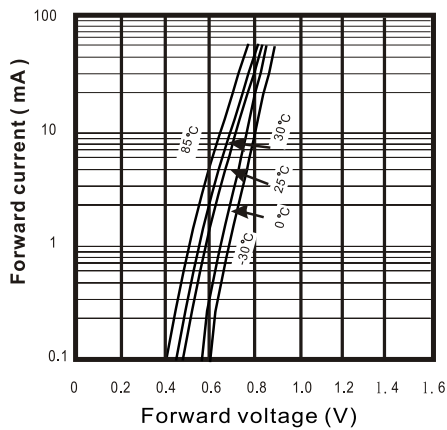


Fig. 2 - Reverse characteristics(P Type)

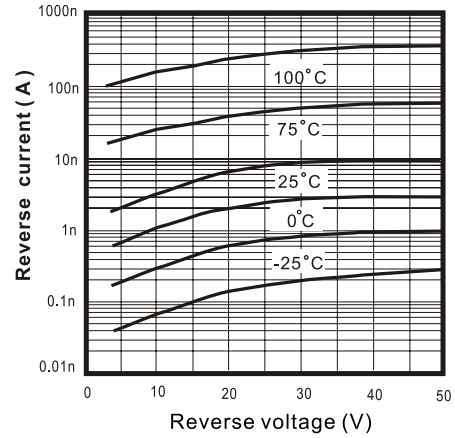


Fig. 3 - Forward characteristics(N Type)

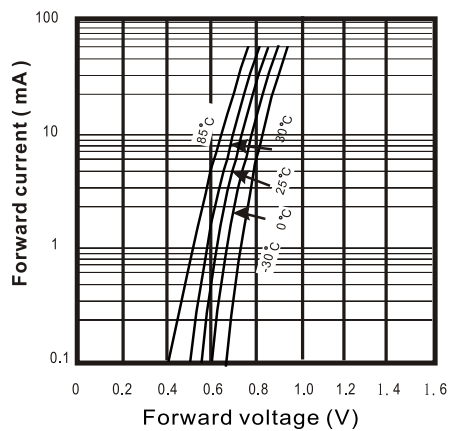


Fig. 4 - Reverse characteristics(N Type)

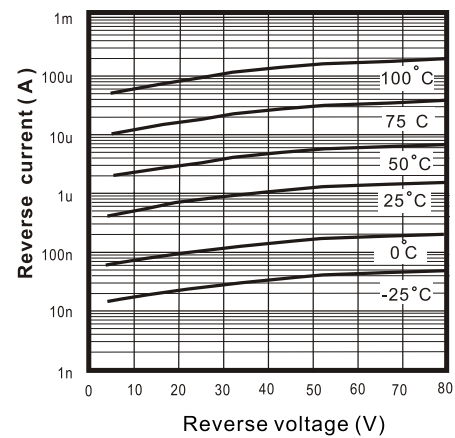


Fig. 5 - Capacitance between terminals characteristics

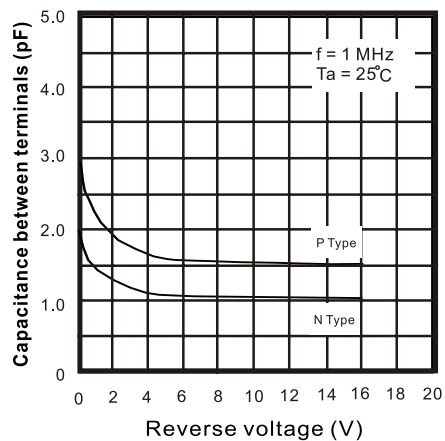


Fig. 6 - Power attenuation curve

